

MOSFET – N-Channel, POWERTRENCH[®]

20 V, 6.1 A, 28 mΩ

FDN028N20

General Description

This N-Channel POWERTRENCH MOSFET is produced using onsemi's advanced POWERTRENCH process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

Features

- Max $r_{DS(on)}$ = 28 mΩ at $V_{GS} = 4.5$ V, $I_D = 5.2$ A
- Max $r_{DS(on)}$ = 45 mΩ at $V_{GS} = 2.5$ V, $I_D = 4.4$ A
- High Performance Trench Technology for Extremely Low $r_{DS(on)}$
- High Power and Current Handling Capability in a Widely Used Surface Mount Package
- Fast Switching Speed
- 100% UIL Tested
- This Device is Pb-Free, Halide Free and is RoHS Compliant

Applications

- Primary DC-DC Switch
- Load Switch

MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

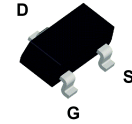
Symbol	Parameter		Ratings	Unit
V_{DS}	Drain to Source Voltage		20	V
V_{GS}	Gate to Source Voltage (Note 3)		± 12	V
I_D	Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	6.1	A
	Pulsed	(Note 5)	52	
E_{AS}	Single Pulse Avalanche Energy (Note 4)		6	mJ
P_D	Power Dissipation	(Note 1a)	1.5	W
		(Note 1b)	0.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

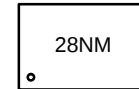
Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	80	$^\circ\text{C}/\text{W}$

V_{DS}	$r_{DS(on)}$ MAX	I_D MAX
20 V	28 mΩ @ 4.5 V	6.1 A
	45 mΩ @ 2.5 V	



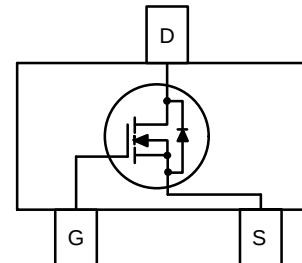
SOT-23/SUPERSOT[™]-23, 3 LEAD, 1.4x2.9
CASE 527AG

MARKING DIAGRAM



28N = Specific Device Code
M = Date Code

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

FDN028N20

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	20	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C	–	15	–	mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\ \text{V}$, $V_{GS} = 0\ \text{V}$	–	–	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = 12\ \text{V}$, $V_{DS} = 0\ \text{V}$	–	–	100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	0.5	0.9	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, referenced to 25°C	–	–3	–	mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 4.5\ \text{V}$, $I_D = 5.2\ \text{A}$	–	23	28	m Ω
		$V_{GS} = 2.5\ \text{V}$, $I_D = 4.4\ \text{A}$	–	32	45	
		$V_{GS} = 4.5\ \text{V}$, $I_D = 5.2\ \text{A}$, $T_J = 125^\circ\text{C}$	–	30	41	
g_{FS}	Forward Transconductance	$V_{DS} = 5\ \text{V}$, $I_D = 5.2\ \text{A}$	–	28	–	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 10\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	–	399	600	pF
C_{oss}	Output Capacitance		–	91	140	pF
C_{rss}	Reverse Transfer Capacitance		–	87	130	pF

SWITCHING CHARACTERISTICS

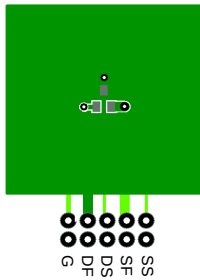
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\ \text{V}$, $I_D = 5.2\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_{GEN} = 6\ \Omega$	–	5	10	ns
t_r	Rise Time		–	2	10	ns
$t_{d(off)}$	Turn-Off Delay Time		–	15	29	ns
t_f	Fall Time		–	2	10	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $4.5\ \text{V}$ $V_{DD} = 10\ \text{V}$, $I_D = 5.2\ \text{A}$	–	4.3	6.0	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $2.5\ \text{V}$ $V_{DD} = 10\ \text{V}$, $I_D = 5.2\ \text{A}$	–	2.8	3.9	nC
Q_{gs}	Gate to Source Charge	$V_{DD} = 10\ \text{V}$, $I_D = 5.2\ \text{A}$	–	0.7	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	1.6	–	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

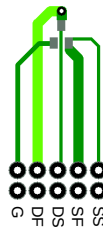
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}$, $I_S = 5.2\ \text{A}$ (Note 2)	–	0.85	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 5.2\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$	–	13	27	ns
Q_{rr}	Reverse Recovery Charge		–	3	10	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $80^\circ\text{C}/\text{W}$ when mounted on a $1\ \text{in}^2$ pad of 2 oz copper.



b. $180^\circ\text{C}/\text{W}$ when mounted on a minimum pad.

- Pulse Test: Pulse Width $< 300\ \mu\text{s}$, Duty Cycle $< 2.0\%$.
- As an N-ch device, the negative V_{GS} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.
- E_{AS} of 6 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3\ \text{mH}$, $I_{AS} = 2\ \text{A}$, $V_{DD} = 20\ \text{V}$, $V_{GS} = 10\ \text{V}$. 100% test at $L = 0.1\ \text{mH}$, $I_{AS} = 7\ \text{A}$.
- Pulsed I_D please refer to Figure 10 SOA graph for more details.

TYPICAL CHARACTERISTICS

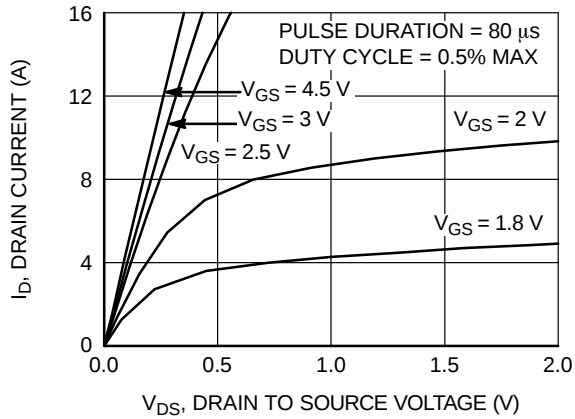
(T_J = 25°C unless otherwise noted)

Figure 1. On Region Characteristics

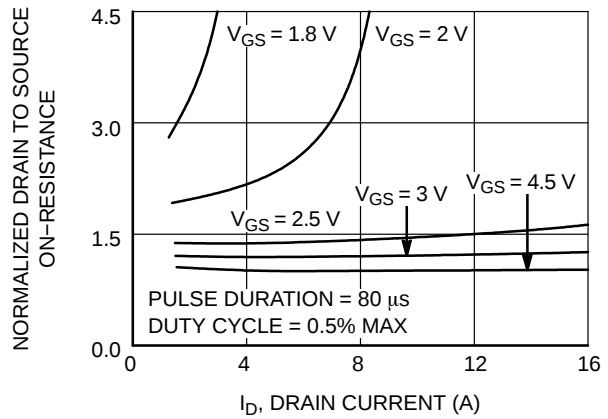


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

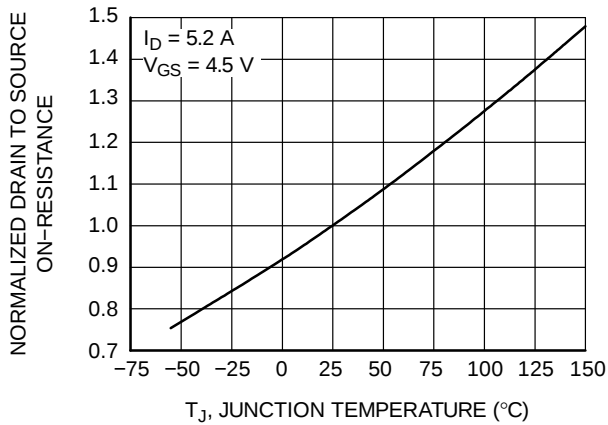


Figure 3. Normalized On-Resistance vs. Junction Temperature

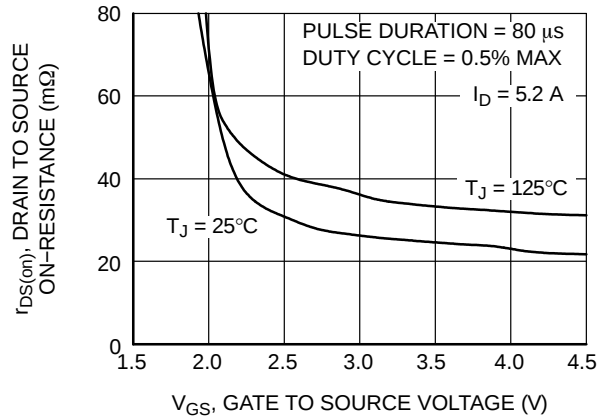


Figure 4. On-Resistance vs. Gate to Source Voltage

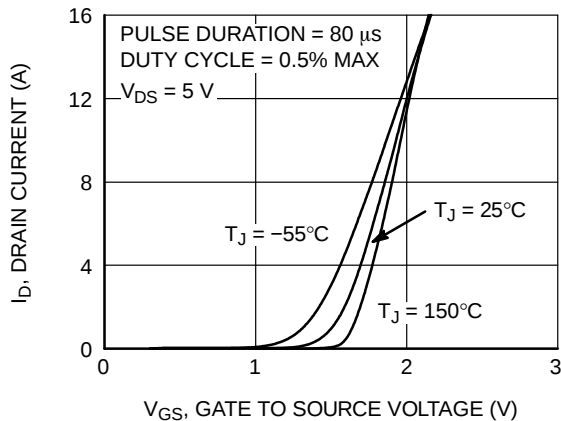


Figure 5. Transfer Characteristics

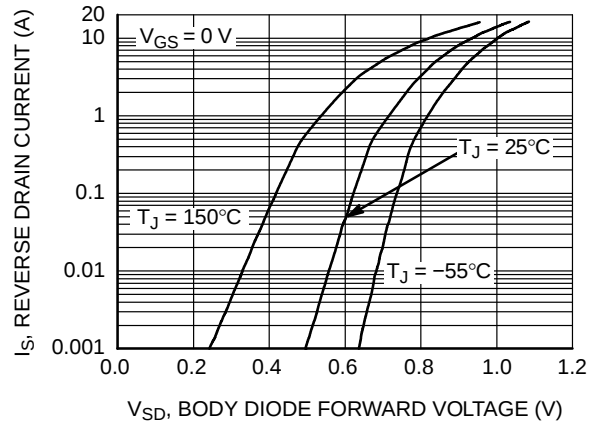


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS

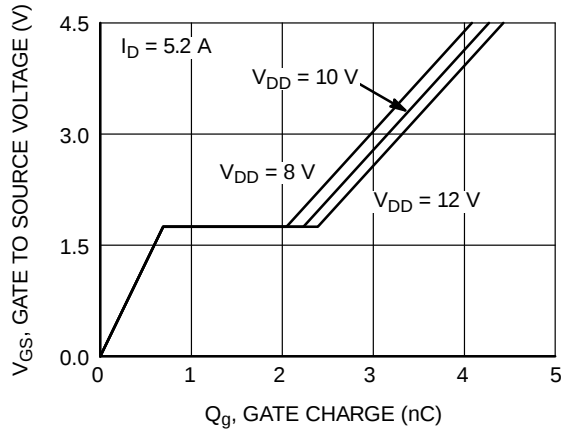
(T_J = 25°C unless otherwise noted) (continued)

Figure 7. Gate Charge Characteristics

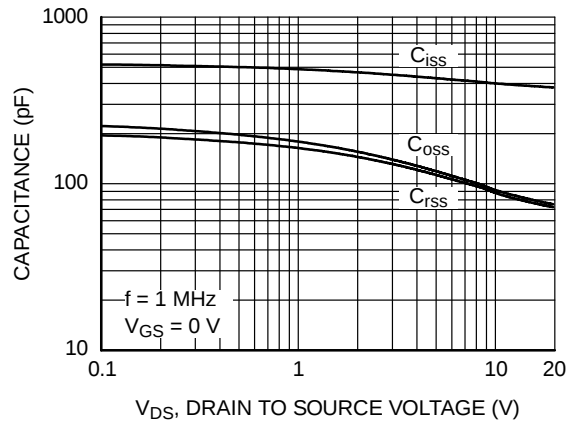


Figure 8. Capacitance vs. Drain to Source Voltage

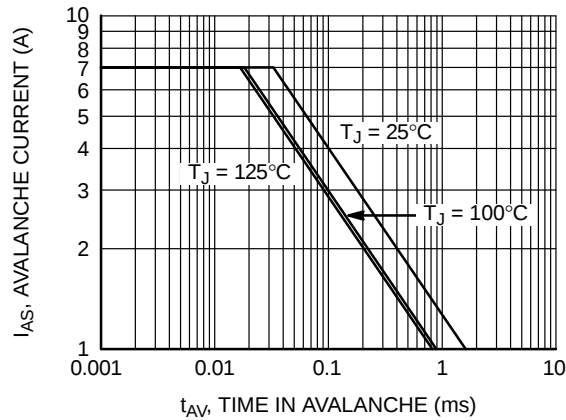


Figure 9. Unclamped Inductive Switching Capability

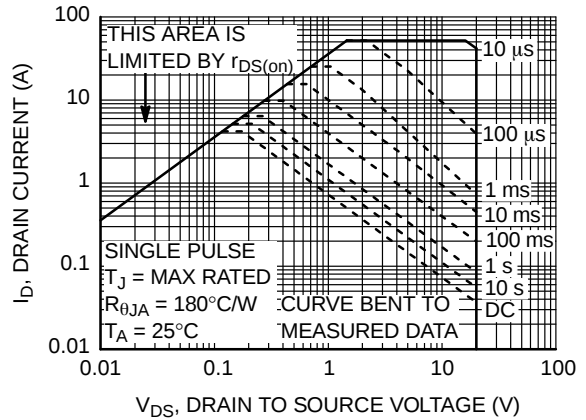


Figure 10. Forward Bias Safe Operating Area

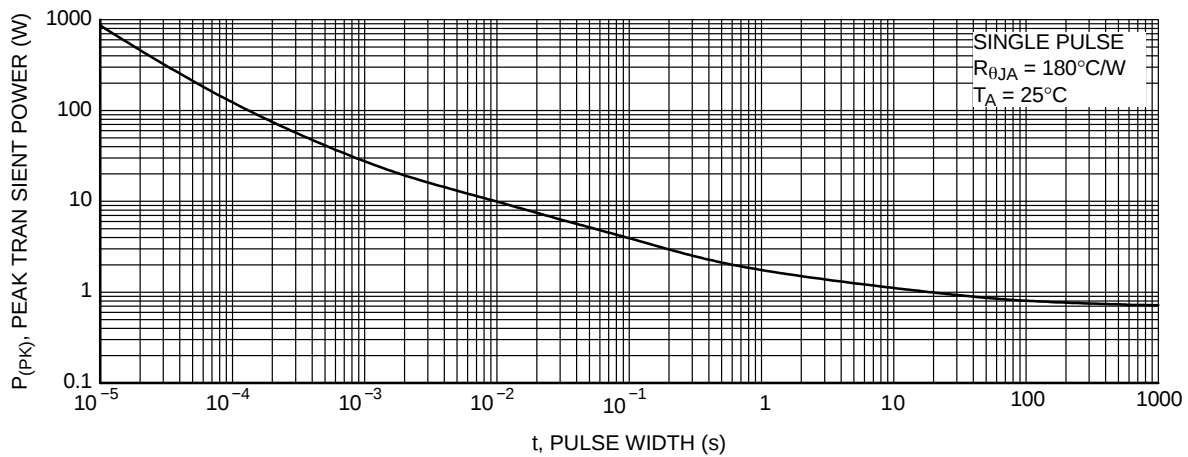


Figure 11. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS

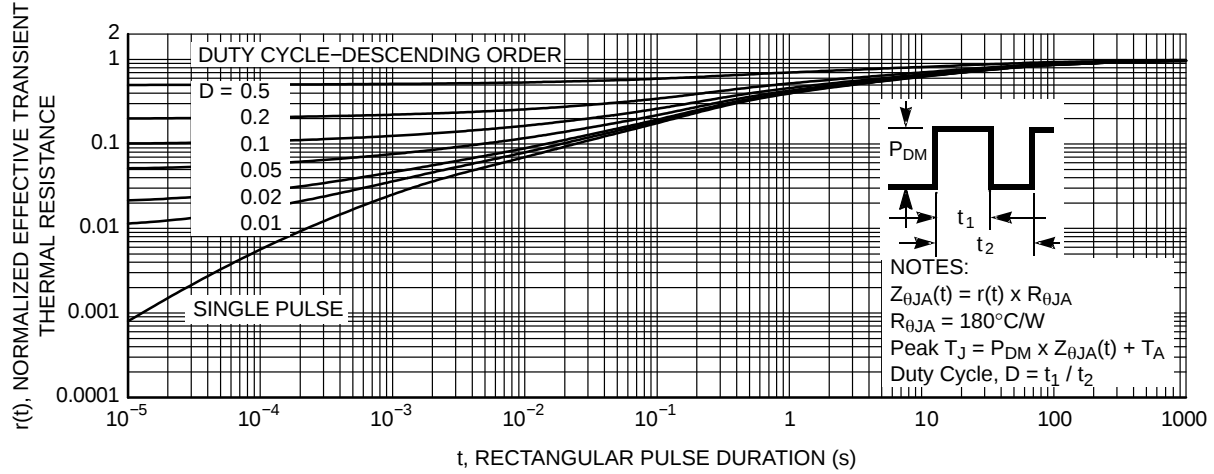
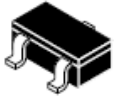
(T_J = 25°C unless otherwise noted) (continued)

Figure 12. Junction-to-Ambient Transient Thermal Response Curve

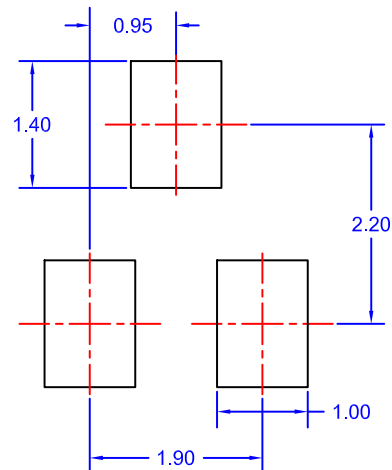
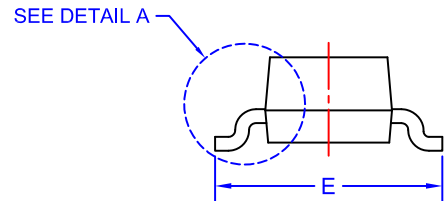
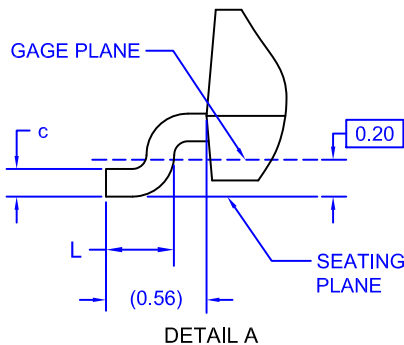
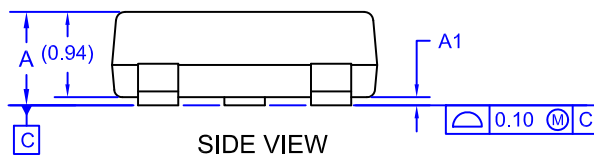
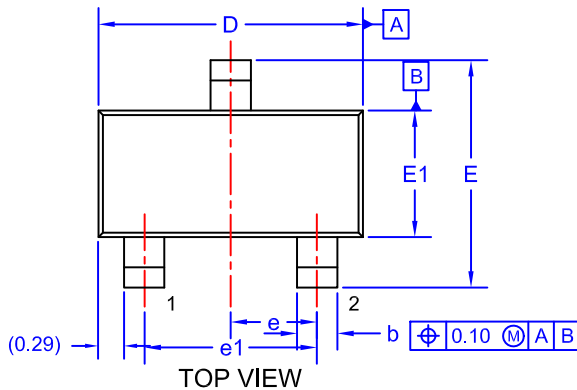
PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Shipping [†]
FDN028N20	28N	SOT-23/SUPERSOT-23, 3 LEAD, 1.4x2.9 (Pb-Free, Halide Free)	7"	8 mm	3000 / Tape & Reel

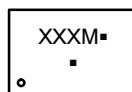
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.


SOT-23/SUPERSOT™ –23, 3 LEAD, 1.4x2.9
CASE 527AG
ISSUE A

DATE 09 DEC 2019



*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*


XXX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-23/SUPERSOT-23, 3 LEAD, 1.4X2.9	PAGE 1 OF 1

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